



Silicon Power Schottky Diode

MBRT60045 thru MBRT600100R

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 600\text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}
- Isolation Type Package

Three Tower Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRT60045 (R)	MBRT60060 (R)	MBRT60080 (R)	MBRT600100 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		45	60	80	100	V
RMS reverse voltage	V_{RMS}		32	42	57	70	V
DC blocking voltage	V_{DC}		45	60	80	100	V
Continuous forward current	I_F	$T_C \leq 100\text{ °C}$	600	600	600	600	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	4000	4000	4000	4000	A
Operating temperature	T_j		-40 to 150	-40 to 150	-40 to 150	-40 to 150	°C
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBRT60045 (R)	MBRT60060(R)	MBRT60080 (R)	MBRT600100 (R)	Unit
Diode forward voltage	V_F	$I_F = 300\text{ A}$, $T_j = 25\text{ °C}$	0.75	0.8	0.88	0.88	V
Reverse current	I_R	$V_R = 20\text{ V}$, $T_j = 25\text{ °C}$	1	1	1	1	mA
		$V_R = 20\text{ V}$, $T_j = 125\text{ °C}$	20	20	20	20	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.12	0.12	0.12	0.12	°C/W
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